

**Amendments to the Claims**

1. *(Currently Amended)* A voltage driver circuit for driving a device at a selected one of a plurality of voltages associated with respective device operations including a high voltage operation and a relatively lower voltage operation, the driver circuit comprising an input (IN), a single output (OUT) for connection to said device, and a plurality of voltage drivers between said input and said output including at least one high voltage breakdown driver (~~10~~) and at least one relatively lower breakdown voltage driver (~~Q7, Q8~~), the circuit being arranged such that, during a high voltage operation, said high voltage breakdown driver (~~10; Q1, Q2; Q3, Q4~~) is connected to said output and there is a substantially zero voltage drop across said relatively lower breakdown voltage driver, and, during a relatively lower voltage operation, said relatively lower breakdown voltage driver (~~Q7, Q8~~) provides the drive voltage for driving said device, the contribution of said high breakdown voltage driver to said drive voltage during said relatively lower voltage operation being substantially negligible.

2. *(Currently Amended)* A circuit according to claim 1, wherein the high voltage breakdown drivers comprise inverters consisting of high voltage breakdown transistors (~~Q1, Q2, Q3, Q4~~).

3. *(Currently Amended)* A circuit according to ~~claim 1 or claim 2~~ claim 1, wherein the at least one relatively lower breakdown voltage driver comprises an inverter consisting of relatively lower breakdown voltage transistors (~~Q7, Q8~~).

4. *(Currently Amended)* A circuit according to ~~any one of claims 1 to 3~~ claim 1, comprising two signal paths between the input and the output, a first signal path consisting of one or more high voltage drivers (~~10; Q1, Q2; Q3, Q4~~) connected in series, and a second signal path consisting of at least one low voltage driver (~~Q7, Q8~~), the first and second signal paths being connected in parallel to one another.

5. *(Original)* A circuit according to claim 4, comprising means for selecting the first signal path during high voltage operation.

6. *(Currently Amended)* A voltage driver circuit for driving a device at a selected one of a plurality of voltages associated with respective device operations including a high voltage operation and a relatively lower voltage operation, the driver circuit comprising an input (IN), a single output (OUT) for connection to said device, and a plurality of voltage drivers between said input and said output including at least one high voltage breakdown driver ~~(I0)~~ and at least one relatively lower breakdown voltage driver ~~(Q7, Q8)~~, the high breakdown voltage driver comprising a voltage level shifter which is connected at the input of the circuit between first and second voltage lines, the output of said level shifter ~~(Q1-B-Q6)~~ being connected to the input of a relatively lower breakdown voltage driver ~~(Q9, Q10)~~ connected to the output between said first and second voltage lines ~~(POS, NEG)~~.

7. *(Original)* A circuit according to claim 6, wherein said voltage level shifter comprises a partial level shifter.

8. *(Currently Amended)* A circuit according to ~~claim 6 or claim 7~~ claim 6, wherein the relatively lower breakdown voltage driver comprises an inverter consisting of thick gate oxide devices ~~(Q9, Q10)~~.

9. *(Currently Amended)* A circuit according to claim 8, wherein the thick gate oxide devices comprise GO<sub>2</sub> devices ~~(Q9, Q10)~~.

10. *(Currently Amended)* A circuit according to ~~any one of claims 6 to 9~~ claim 6, wherein said at least one relatively lower breakdown voltage driver comprises an I/O protection inverter.

11. *(Currently Amended)* A circuit according to ~~any one of claims 6 to 10~~ claim 6, wherein a high voltage pull-up or pull-down transistor ~~(Q11)~~ is provided between the output and the first or second voltage lines respectively.

12. *(Currently Amended)* A memory device, comprising a voltage driver circuit according to ~~any one of the claims 1 to 11~~ claim 1.

13. *(Original)*                    An integrated circuit, comprising or including a memory device according to claim 12.

14. *(Original)*                    A computing system, including an integrated circuit according to claim 13.